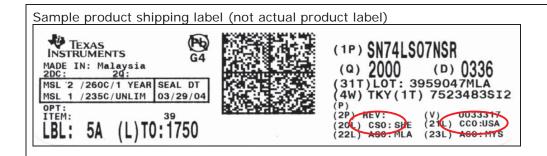
PCN Nu	mber:	PCN20130513000		I	PCN Da	te:	05/15/2013		
Title:		of Aizu Facility as a vices in the 50HPA07			or se	elect dev	vices	in the	
Custom	er Contact:	PCN Manager	Phone: +	1(214)480-6037 <b>Dept:</b>			Quality Services		
Propose Date:	ed 1 <sup>st</sup> Ship	1 (18/15/7013	Estimated Availabilit	•		Date provided at sample request.			
Change									
	embly Site	Assembly		_	Assembly Materials				
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	t Site		Shipping/La		_	est Process Vafer Bump Process			
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ท "Prodเ	uct Affected" s	ection.							
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Product Affected:							
Group 1: CMOS9T Process devices, adding Aizu Fab							
LM3565TLE/NOPB	LP5907SNX-1.2/NOPB	LP5907SNX-3.0/NOPB	LP8556TMX-E09/NOPB				
LM3565TLX/NOPB	LP5907SNX-1.8/NOPB	LP5907SNX-3.1/NOPB	LP8556TMX-E09/S1				
LP3925RME-E/NOPB	LP5907SNX-2.7/NOPB	LP5907SNX-3.2/NOPB	LP8556TMX-E09/S7003056				
LP3925RMX-E/NOPB	LP5907SNX-2.8/NOPB	LP5907SNX-3.3/NOPB					
LP5562TME/NOPB	LP5907SNX-2.85/NO	LP5907SNX-4.5/NOPB					
LP5562TMX/NOPB	LP5907SNX-2.85/NOPB	LP8556TME-E09/NOPB					
Group 2: 50HPA07 Process devices, adding Aizu Fab							
OPA4188AID	OPA4188AIDR						

Qualification Plan: (CMOS9T Process)										
This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.										
Qualification Schedule: Sta				03/2013	13 <b>E</b> n		<b>d:</b> 07/2		2013	
Qual Vehicle 1: LP5907UVX-3.3										
Wafer Fab Site: AIZU			Metallization: Al 0.5%Cu 0.50			ı 0.50	05uM			
Wafer Fab Process: CMOS			Wa	fer diameter:	200mm					
Qualification:										
Reliability Test			Conditions				Sample Size/Fail Lot#1 Lot#2 Lot#3			
Life Test			125C (1000 Hrs)				77	/0	77/0	77/0
EFR			125C (48 hrs)				30!	5/0	305/0	305/0
**High Temp. Storage Bake			150C (1000 Hrs)				77	/0	77/0	-
Biased HAST			85C/85%RH (1000 Hrs)				77	/0	77/0	77/0
**Autoclave 121C	12	121C, 2 atm (96 Hrs)				77	/0	77/0	77/0	
**T/C -65C/150C	-6	-65C/+150C (500 Cycles)				77	/0	77/0	77/0	
ESD HBM	Pe	Per JEDEC				3,	/0	3/0	3/0	
ESD CDM	Pe	Per JEDEC				3,	/0	3/0	3/0	
Latch-up	(р	(per JESD78)				6,	/0	6/0	6/0	
** Preconditioning seque	nce:	level	1 @	260C		•				

## Qualification Data: (50HPA07 Process) Approved 6/3/2011 This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications. Qual Vehicle 1: TMP431BDGK Metallization: 0.2kÅTi/0.425kÅTiN/5.4kÅAlCu0.5%/0.275kÅTiN Wafer Fab Site: AI7U Wafer Fab Process: 50HPA07 Wafer diameter: 200mm Qualification: Plan X Test Results Sample Size/Fail Conditions Reliability Test Lot#1 Lot#3 Lot#2 Life Test 150C (300 Hrs) 77/0 77/0 **Electrical Characterization** Over temp Pass Pass \*\*Biased HAST 130C/85%RH (96 Hrs) 77/0 77/0 \*\*Unbiased HAST 130C/85%RH/33.3 psia (96 Hrs) 77/0 77/0 \*\*T/C -65C/150C -65C/+150C (500 Cycles) 77/0 77/0 **ESD HBM** Per JEDEC 3/0 \_ ESD CDM Per JEDEC 3/0 Wafer level Reliability Per Site Specification Pass Pass Pass (per JESD78) 6/0 Latch-up \_ Manufacturability (per mfg. Site specification) Pass Pass \*\* Preconditioning sequence: level 2 @ 260C Oual Vehicle 2: OPA2333AIDGK Wafer Fab Site: AIZU Metallization: Ti/TiN/AlCu .5 Wafer Fab Process: 50HPA07 Wafer diameter: 200mm Qualification: Plan Test Results Sample Size/Fail Reliability Test Conditions Lot#3 Lot#1 Lot#2 Life Test 150C (300 Hrs) 77/0 **Electrical Characterization** Over temp Pass \*\*Biased HAST 130C/85%RH (96 Hrs) 80/0 \*\*Unbiased HAST 130C/85%RH/33.3 psia (96 Hrs) 80/0 \*\*T/C -65C/150C -65C/+150C (500 Cycles) 80/0 **ESD HBM** Per JEDEC 3/0 \_ **ESD CDM** 3/0 Per JEDEC Manufacturability (Wafer Fab) (per mfg. Site specification) Pass Latch-up (per JESD78) 6/0 Manufacturability (Assembly) (per mfg. Site specification) Pass Wafer Level Reliability (per mfg. Site specification) Pass \*\* Preconditioning sequence: level 2 @ 260C

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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USA	PCNAmericasContact@list.ti.com
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